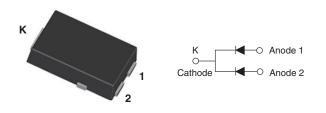
### **Vishay Semiconductors**





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SMPC (TO-277A)

PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	2 x 3 A				
V <sub>R</sub>	100 V				
V <sub>F</sub> at I <sub>F</sub>	0.75 V				
t <sub>rr (typ.)</sub>	27 ns				
T <sub>J</sub> max.	175 °C				
Package	SMPC (TO-277A)				
Circuit configuration	Dual serial				

### FEATURES

- Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="http://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage		V <sub>RRM</sub>		100	V		
Average restified forward surrent	per device	I <sub>F(AV)</sub>	T <sub>Sp</sub> = 165 °C	6			
Average rectified forward current	per diode			3	A		
Non repetitive peak ourse oursent	per device	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 6 ms square pulse	150			
Non-repetitive peak surge current	per diode			80			
Operating junction and storage temperatures		T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	100	-	-	v	
Forward valtage, per diade	V <sub>F</sub>	I <sub>F</sub> = 3 A	-	0.87	0.94		
Forward voltage, per diode		I <sub>F</sub> = 3 A, T <sub>J</sub> = 125 °C	-	0.75	0.79		
Deverse lectrose current, per diada	I <sub>R</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	-	2	μA	
Reverse leakage current, per diode		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	0.7	10		
Junction capacitance	CT	V <sub>R</sub> = 100 V	-	13	-	pF	

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RoHS

COMPLIANT

HALOGEN

FREE



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## **Vishay Semiconductors**

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t <sub>rr</sub>	$I_F=1~A,~dI_F/dt=50~A/\mu s,~V_R=30~V$		-	27	-			
Povereo recover timo		$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	25			
Reverse recovery time		T <sub>J</sub> = 25 °C		-	20	-	A nC		
		T <sub>J</sub> = 125 °C	I <sub>F</sub> = 3 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 160 V	-	26	-			
Deals receiver sourcent	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	2.4	-			
Peak recovery current		T <sub>J</sub> = 125 °C		-	3.8	-			
	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	23	-			
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	50	-			

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C	
Thermal resistance, junction to solder pad, per diode	R <sub>thJ-Sp</sub>		-	2.8	4	°C/W	
Approvimeto weight				0.1		g	
Approximate weight				0.0035		oz.	
Marking device		Case style SMPC (TO-277A)		NC	H1		

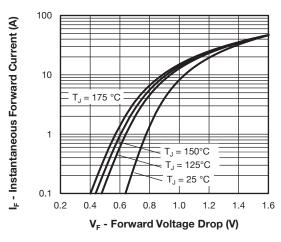


Fig. 1 - Typical Forward Voltage Drop Characteristics

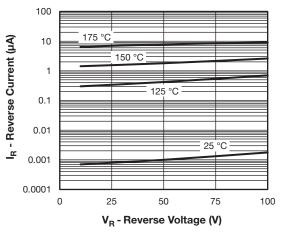
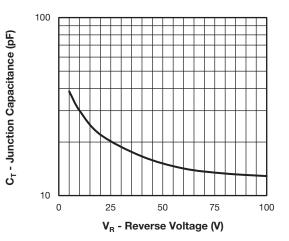


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

## VS-6CSH01HM3

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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

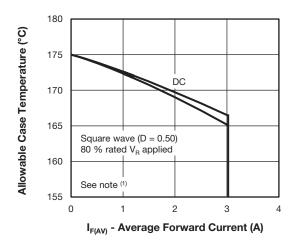
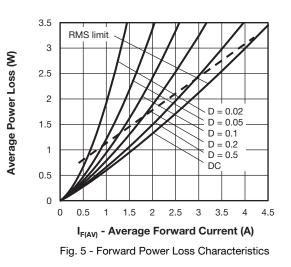


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current



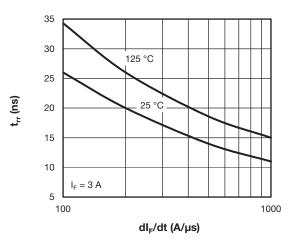


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

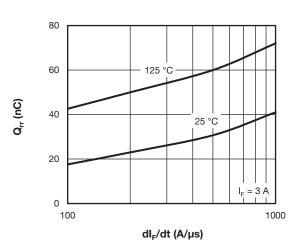


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$ 

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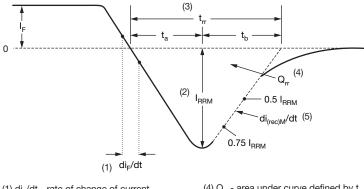
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# VS-6CSH01HM3

## **Vishay Semiconductors**



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{\text{RRM}}$  peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.

(4)  ${\rm Q}_{\rm rr}$  - area under curve defined by  ${\rm t}_{\rm rr}$  and  ${\rm I}_{\rm RRM}$ 

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 8 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

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Device code

le	vs-	•	6	с	S	н	01	н	М3							
I	1		2	3	4	5	6	(7)	8							
	1 - Vishay Semiconductors product															
	2	-	Cur	rent rati	ng (6 = )	6 A)										
	3	-	Circ	cuit conf	iguratior	า:										
			C =	C = common cathode												
	4	-	S =	S = SMPC package												
	5	-	Pro	Process type,												
		H = hyper fast recovery														
	6	-	Volt	Voltage code (01 = 100 V)												
	7	-	H =	H = AEC-Q101 qualified												
	8	-	M3	= halog	en-free,	RoHS-0	complia	nt, and	termina	M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free						

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-6CSH01HM3/86A	1500	1500	7" diameter plastic tape and reel				
VS-6CSH01HM3/87A	6500	6500	13" diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95570				
Part marking information	www.vishay.com/doc?95565				
Packaging information	www.vishay.com/doc?88869				
SPICE model	www.vishay.com/doc?96378				

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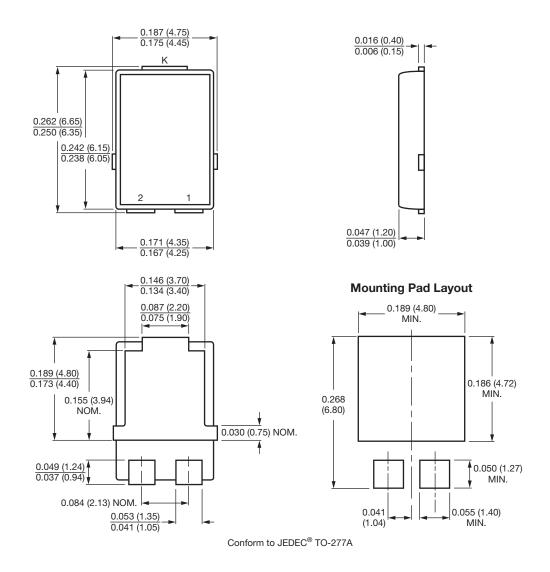
## **Outline Dimensions**





TO-277A (SMPC)

#### **DIMENSIONS** in inches (millimeters)





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